Hironori Okumura

List of Publications by Year
in descending order

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		759233	580821
28	598	12	25
papers	citations	h-index	g-index

28	28	28	864
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Impurity diffusion in ion implanted AlN layers on sapphire substrates by thermal annealing. Japanese Journal of Applied Physics, 2022, 61, 026501.	1.5	8
2	Photo-induced conductivity transient in n-type Î²-(Al0.16Ga0.84)2O3 and Î²-Ga2O3. Japanese Journal of Applied Physics, 2021, 60, SBBD15.	1.5	2
3	Electrical properties of heavily Sn-doped (AlGa)2O3 layers on Î²-Ga2O3 (010) substrates. Japanese Journal of Applied Physics, 2021, 60, 065504.	1.5	2
4	Optical and electrical properties of silicon-implanted Î±-Al₂O₃. Japanese Journal of Applied Physics, 2021, 60, 106502.	1.5	2
5	Growth of double-barrier Î²-(AlGa)₂O₃/Ga₂O₃ structure and heavily Sn-doped Ga₂O₃ layers using molecular-beam epitaxy. Japanese Journal of Applied Physics, 2020, 59, 075503.	1.5	2
6	Nitrogen-Polar Polarization-Doped Field-Effect Transistor Based on Al_{0.8}Ga_{0.2}N/AlN on SiC With Drain Current Over 100 mA/mm. IEEE Electron Device Letters, 2019, 40, 1245-1248.	3.9	32
7	Dry and wet etching for Î²-Ga₂O₃ Schottky barrier diodes with mesa termination. Japanese Journal of Applied Physics, 2019, 58, 120902.	1.5	33
8	Fabrication of an AlN ridge structure using inductively coupled Cl₂/BCl₃ plasma and a TMAH solution. Japanese Journal of Applied Physics, 2019, 58, 026502.	1.5	9
9	Demonstration of lateral field-effect transistors using Sn-doped Î²-(AlGa)₂O₃ (010). Japanese Journal of Applied Physics, 2019, 58, SBBD12.	1.5	29
10	AlN metalâ€“semiconductor field-effect transistors using Si-ion implantation. Japanese Journal of Applied Physics, 2018, 57, 04FR11.	1.5	42
11	N-polar AlN buffer growth by metalâ€“organic vapor phase epitaxy for transistor applications. Applied Physics Express, 2018, 11, 101002.	2.4	16
12	Vertical GaN Junction Barrier Schottky Rectifiers by Selective Ion Implantation. IEEE Electron Device Letters, 2017, 38, 1097-1100.	3.9	136
13	Vacancy-type defects in Mg-doped GaN grown by ammonia-based molecular beam epitaxy probed using a monoenergetic positron beam. Journal of Applied Physics, 2016, 119, 245702.	2.5	9
14	Low p-type contact resistance by field-emission tunneling in highly Mg-doped GaN. Applied Physics Letters, 2016, 109, .	3.3	11
15	Systematic investigation of the growth rate of Î²-Ga₂O₃(010) by plasma-assisted molecular beam epitaxy. Applied Physics Express, 2014, 7, 095501.	2.4	122
16	Formation mechanism of threading-dislocation array in AlN layers grown on 6H-SiC (0001) substrates with 3-bilayer-high surface steps. Applied Physics Letters, 2014, 105, .	3.3	14
17	Coherent Growth of AlN/GaN Short-Period Superlattice with Average GaN Mole Fraction of up to 20% on 6H-SiC(0001) Substrates by Plasma-Assisted Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JE21.	1.5	4
18	Optical Properties of Highly Strained AlN Coherently Grown on 6H-SiC(0001). Applied Physics Express, 2013, 6, 062604.	2.4	12

#	Article	IF	Citations
19	Over-700-nm Critical Thickness of AlN Grown on 6H-SiC(0001) by Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 105502.	2.4	26
20	AlN/GaN Short-Period Superlattice Coherently Grown on 6H-SiC(0001) Substrates by Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 051002.	2.4	3
21	Growth of Nitrogen-Polar 2H-AlN on Step-Height-Controlled 6H-SiC(0001Ì„) Substrate by Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BH02.	1.5	1
22	Growth of Nitrogen-Polar 2H-AlN on Step-Height-Controlled 6H-SiC(0001Ì„) Substrate by Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BH02.	1.5	3
23	Reduction of Threading Dislocation Density in 2H-AlN Grown on 6H-SiC(0001) by Minimizing Unintentional Active-Nitrogen Exposure before Growth. Applied Physics Express, 2011, 4, 025502.	2.4	29
24	Enhancement of initial layer-by-layer growth and reduction of threading dislocation density by optimized Ga pre-irradiation in molecular-beam epitaxy of 2H-AlN on 6H-SiC(0001). Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2094-2096.	0.8	14
25	In situGravimetric Monitoring of Thermal Decomposition and Hydrogen Etching Rates of 6H-SiC(0001) Si Face. Japanese Journal of Applied Physics, 2009, 48, 095505.	1.5	5
26	Observation of novel defect structure in 2H-AlN grown on 6H-SiC(0001) substrates with 3-bilayer-height step-and-terrace structures. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1187-1189.	1.8	5
27	Impact of surface step heights of 6Hâ€“SiC (0001) vicinal substrates in heteroepitaxial growth of 2Hâ€“AlN. Applied Surface Science, 2008, 254, 7858-7860.	6.1	26
28	Photoconductivity buildup and decay kinetics in unintentionally doped Î²-Ga₂O₃. Japanese Journal of Applied Physics, 0, , .	1.5	1